

Features

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R_{DS(ON)}
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

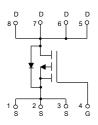
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 39°C/W Junction to Ambient(Note2)
- Thermal Resistance: 3.2°C/W Junction to Case

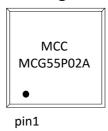
Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Volltage		V _{GS}	±10	V	
Continuous Drain Current	T _C =25°C	. I _D	-55	А	
	T _C =100°C	ַ ט י	-35		
Pulsed Drain Current ^(Note3)		I _{DM}	-160	Α	
Total Power Dissipation ^(Note4)		P _D	39	W	
Single Pulsed Avalanche Energy ^(Note5)		E _{AS}	98	mJ	

Note:

- Halogen free "Green" products are defined as those which contain <900ppm bromine,
 <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t ≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4. P_{D} is based on max. junction temperature, using junction-case thermal resistance.
- 5. T_J =25°C, V_{DD} =-20V, V_{GS} =-8V, L=1mH

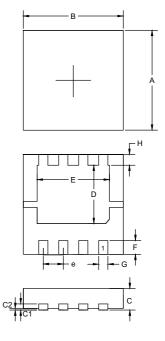
Internal Structure and Marking Code





P-CHANNEL MOSFET

DFN3333



DIMENSIONS						
DIM INCHE		HES	HES MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOIL	
Α	0.126	0.130	3.20	3.30		
В	0.126	0.130	3.20	3.30		
С	0.030	0.033	0.75	0.85		
C1	0.007	0.009	0.18	0.22		
C2		0.002		0.05		
D	0.071	0.079	1.80	2.00		
Е	0.087	0.098	2.20	2.50		
F	0.016	0.020	0.40	0.50		
G	0.010	0.014	0.25	0.35		
Н	0.012	0.016	0.30	0.40		
е	0.024	0.028	0.60	0.70		

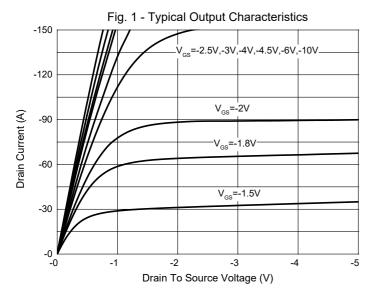


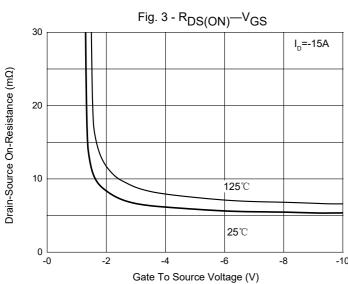
Electrical Characteristics @ 25°C (Unless Otherwise Specified)

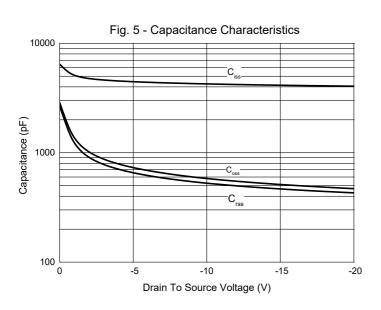
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics	1				1	I	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-20			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±10V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.62	-1.0	V	
		V _{GS} =-4.5V, I _D =-15A		6.5	8.3	mΩ	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-2.5V, I _D =-10A		8	10		
		V _{GS} =-1.8V, I _D =-8A		10.3	15		
Gate Resistance	R_g	F=1 MHz, Open drain		6.6		Ω	
Diode Characteristics						1	
Continuous Body Diode Current	Is				-55	Α	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =-15A			-1	V	
Reverse Recovery Time	t _{rr}	I _F =-6A, dI _F /dt=100A/μs		122		ns	
Reverse Recovery Charge	Q _{rr}	1 _F =-0A, α1 _F /αι=100A/μS		243		nC	
Dynamic Characteristics							
Input Capacitance	C _{iss}			4231			
Output Capacitance	C _{oss}	V _{DS} =-10V,V _{GS} =0V,f=1MHz		583		pF	
Reverse Transfer Capacitance	C _{rss}			527			
Total Gate Charge	Q_g			107			
Gate-Source Charge	Q _{gs}	V _{DS} =-15V,V _{GS} =-10V,I _D =-9.1A		4.7		nC	
Gate-Drain Charge	Q_{gd}			15			
Turn-On Delay Time	t _{d(on)}			7.6			
Turn-On Rise Time	t _r	V _{DS} =-15V, V _{GEN} =-10V,		11			
Turn-Off Delay Time	t _{d(off)}	$R_G=2.5\Omega$, $I_{DS}=-6A$		347		- ns -	
Turn-Off Fall Time	t _f			136			

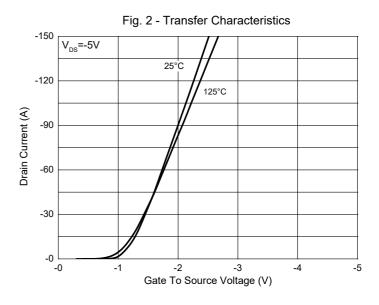


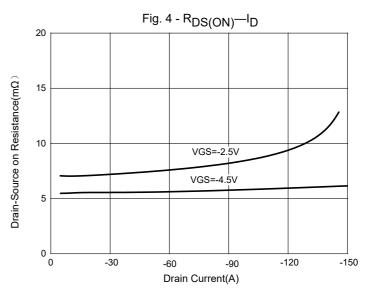
Curve Characteristics

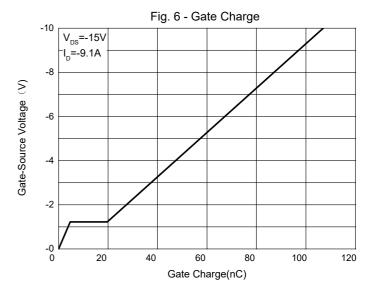






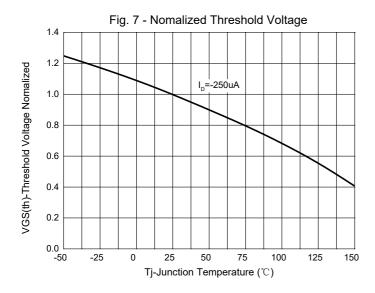


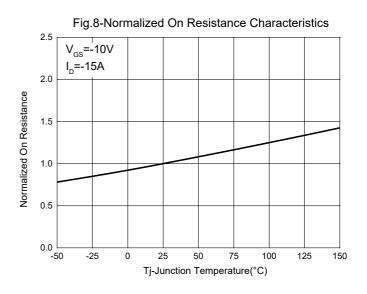


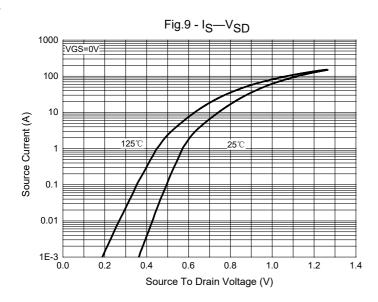


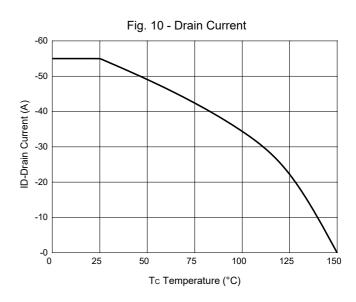


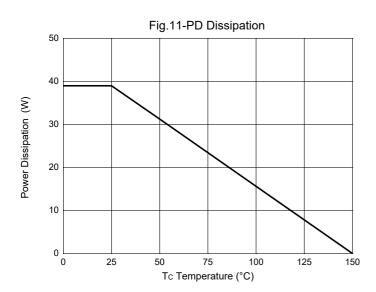
Curve Characteristics





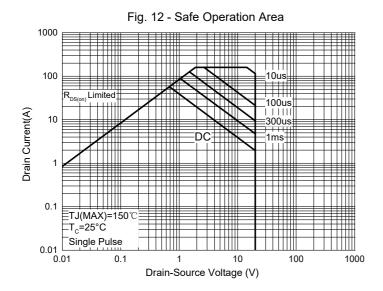


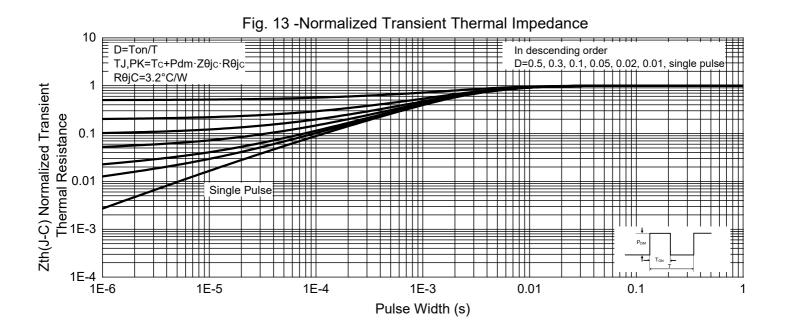






Curve Characteristics





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Ordering Information

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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